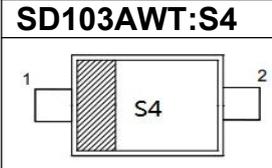
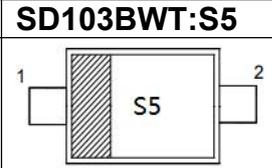
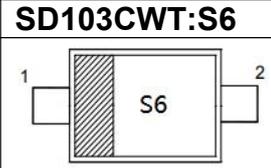


Surface Mount Schottky Barrier Diodes

Features

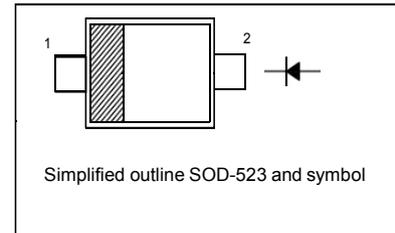
- Low Forward Voltage

MARKING

SD103AWT:S4	SD103BWT:S5	SD103CWT:S6
		

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage	V_{RRM}	SD103AWT SD103BWT SD103CWT	40 30 20	V	
Reverse Voltage		V_R	SD103AWT SD103BWT SD103CWT	40 30 20	V
Average Forward Rectified Current			$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$	I_{FSM}		2	A	
Power Dissipation	P_{tot}	150	mW		
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$		

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	SD103AWT SD103BWT SD103CWT	40 30 20	- - -	V	
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$		I_R	SD103AWT SD103BWT SD103CWT	- - -	5 5 5	μA
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$			V_F	- -	- -	0.37 0.6
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T			-	50	-
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	10	-	ns	

Typical Characteristics

